

REMARKS

Applicant respectfully requests reconsideration in view of the foregoing amendments and the following remarks. Claims 1-7 were previously pending in this application. Claim 1 has been amended. As a result, claims 1-7 are pending for examination with claim 1 being the sole independent claim. No new matter has been added.

Applicant acknowledges the courtesies extended by Examiner Rao during a telephone interview with the undersigned on December 6, 2007. The substance of the interview is summarized in the remarks set forth herein below.

Rejections under 35 U.S.C. §102 and §103

Claims 1-7 stand rejected under 35 U.S.C. §102(b) as being anticipated by Kazuki (JP 2002-359189) or, in the alternative, under 35 U.S.C. §103(a) as obvious over Kazuki in view of Tuppen (US Patent No. 5,279,687). As discussed during the interview, Applicant has amended claim 1 to further define the claimed subject matter over Kazuki and Tuppen.

Independent claim 1 is directed to a method for forming, by epitaxy, a heteroatomic single-crystal semiconductor layer on a single-crystal semiconductor wafer, the crystal lattices of the layer and of the wafer being different. The method includes first forming in the wafer surface, before epitaxy, at least one ring of discontinuities around a useful region of the wafer by forming at least one rough area in the wafer surface around the useful region. As amended, the rough area includes a plurality of surface irregularities distributed over the wafer surface within the ring of discontinuities.

Claim 1 comprises forming a ring of discontinuities around a useful region of a wafer by forming a rough area in the wafer surface around the useful region. As discussed during the interview, forming a ring of discontinuities by forming “a rough area” is different from forming a trench or channel in the surface wafer as disclosed by Kazuki and Tuppen. In this regard, forming a rough area involves forming a plurality of irregularities on the wafer surface. During the interview, the Examiner recognized the distinction between forming a rough area on the wafer surface and forming a channel or trench in the surface. The Examiner agreed that

amending claim 1 to clarify that a rough area includes a plurality of irregularities distributed over the wafer surface would distinguish over Kazuki and Tuppen.

In view of the forgoing, Applicant respectfully submits that claim 1 patentably distinguishes over Kazuki, either alone or together with Tuppen, which do not teach or suggest forming a rough area that includes a plurality of irregularities distributed over the wafer surface within the ring of discontinuities. Accordingly, the rejection of claim 1 under both §102 and §103 should be withdrawn.

Claims 2-7 depend either directly or indirectly from claim 1 and are patentable for at least the same reasons. Accordingly, Applicant respectfully requests withdrawal of the rejections of these claims.

CONCLUSION

A Notice of Allowance is respectfully requested. The Examiner is requested to call the undersigned at the telephone number listed below if this communication does not place the case in condition for allowance.

If this response is not considered timely filed and if a request for an extension of time is otherwise absent, Applicant hereby requests any necessary extension of time. If there is a fee occasioned by this response, including an extension fee, that is not covered by an enclosed check, please charge any deficiency to Deposit Account No. 23/2825.

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Respectfully submitted,

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